

1MBH10D-120

Molded IGBT

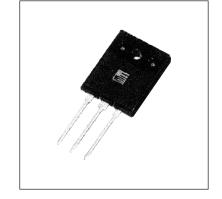
1200V / 10A Molded Package

■ Features

- · Small molded package
- · Low power loss
- · Soft switching with low switching surge and noise
- High reliability, high ruggedness (RBSOA, SCSOA etc.)
- · Comprehensive line-up

■ Applications

- Inverter for Motor drive
- · AC and DC Servo drive amplifier
- Uninterruptible power supply



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (Tc=25°C)

Items			Symbols	Ratings	Units
Collector-Emitter Voltage			Vces	1200	V
Gate-Emitter Voltage			VGES	±20	V
Collector Current	DC	TC=25℃	IC25	18	Α
		TC=105°C	IC110	10	Α
	1ms	TC=25°C	Icp	48	Α
IGBT Max. Power Dissipation			Pc	155	W
FWD Max. Power Dissipation			Pc	105	W
Operating Temperature			Tj	+150	°C
Storage Temperature			Tstg	-40 to +150	°C
Mounting Screw Torque			-	70	N⋅cm

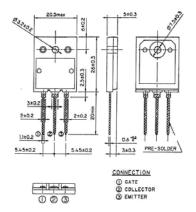
● Electrical Characteristics (at Tc=25°C unless otherwise specified)

Items		Cumbala	Characteristics			Conditions	Haita
		Symbols	min.	typ.	max.	Conditions	Units
Zero gate voltage	Collector Current	Ices	_	_	1.0	VGE = 0V, VCE = 1200V	mA
Gate-Emitter leakage Current		Iges	-	-	20	$V_{CE} = 0V$, $V_{GE} = \pm 20V$	μΑ
Gate-Emitter Threshold Voltage		V _{GE(th)}	5.5	-	8.5	VcE = 20V, Ic = 10mA	V
Collector-Emitter Saturation Voltage		V _{CE(sat)}	_	_	3.5	Vge = 15V, Ic = 10A	V
Input capacitance		Cies	_	1200	_	V _{GE} = 0V	pF
Output capacitance		Coes	_	250	_	Vce = 10V	
Reverse transfer	capacitance	Cres	_	80	_	f = 1MHz	
Switching Time	Turn-on time	ton	_	_	1.2	Vcc = 600V	μs
		tr	_	_	0.6	Ic = 10A V _{GE} = ±15V	
	Turn-off time	toff	_	_	1.5	$R_G = 160\Omega$	
		tf	_	_	0.5	(Half Bridge)	
	Turn-on time	ton	_	0.16	_	Vcc = 600V	
		tr	_	0.11	_	Ic = 10A V _{GE} = +15V	
	Turn-off time	toff	_	0.30	_	$R_G = 16\Omega$	
		tf	_	_	0.50	(Half Bridge)	
FWD forward vol	tage drop	VF	_	_	3.0	IF = 10A	V
Reverse recovery time trr		trr	_	_	0.35	I _F = 10A, V _{GE} = -10V VR = 200V di/dt = 100A/μs	μs

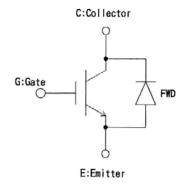
● Thermal resistance Characteristics

Items	Symbols	Characteristics			Conditions	Units
items		min.	typ.	max.	Conditions	Ullits
Thermal resistance	Rth(j-c)	_	_	0.80	IGBT	°C/W
Thermal resistance	Rth(j-c)	_	_	1.19	FWD	

■ Outline drawings, mm



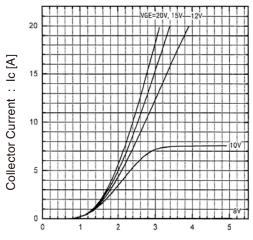
■ Equivalent circuit



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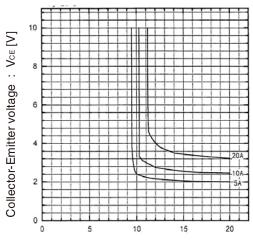
■ Characteristics

Collector current vs. Collector-Emitter voltage $Tj = 25^{\circ}C$



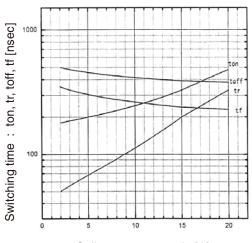
Collector-Emitter voltage: Vce [V]

Collector-Emitter voltage vs. Gate-Emitter Voltage $Tj = 25^{\circ}C$



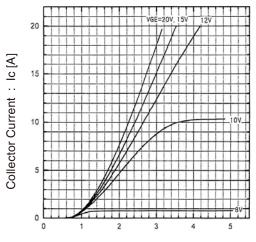
Gate-Emitter voltage: VgE [V]

Switching time vs. Collector current Vcc=600V, $RG=16\Omega$, $VgE=\pm15V$, $Tj=25^{\circ}C$



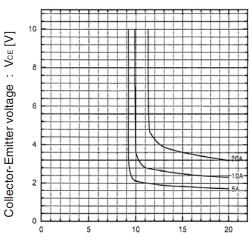
Collector current: Ic [A]

Collector current vs. Collector-Emitter voltage $Tj = 125^{\circ}C$



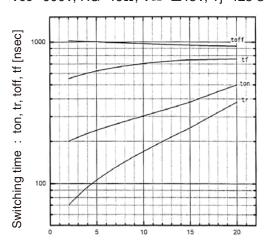
Collector-Emitter voltage : $V_{CE}[V]$

Collector-Emitter voltage vs. Gate-Emitter Voltage $Tj = 125^{\circ}C$



Gate-Emitter voltage: VgE [V]

Switching time vs. Collector current Vcc=600V, RG=16 Ω , V_{GE}= \pm 15V, Tj=125 $^{\circ}$ C

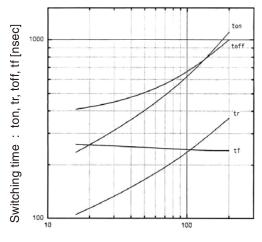


Collector current: Ic [A]

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■ Characteristics

Switching time vs. RG Vcc=600V, IC=10A, VGE= \pm 15V, Tj=25°C



Gate resistance : RG $[\Omega]$

Dynamic input characteristics

Tj=25°C

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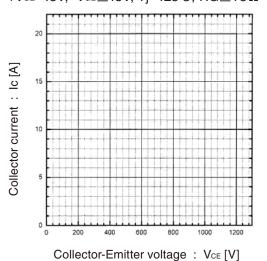
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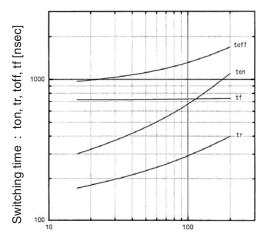
100

Gate charge: Qg [nQ]

Reverse Biased Safe Operating Area +VgE=15V, -VgE≦15V, Tj=125°C, RG≧16Ω

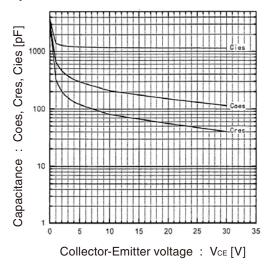


Switching time vs. RG Vcc=600V, IC=10A, VGE= \pm 15V, Tj=125°C



Gate resistance : $RG[\Omega]$

Capacitance vs. Collector-Emitter voltage Tj=25°C



Typical short circuit capability Vcc=800V, RG=16Ω, Tj=125°C

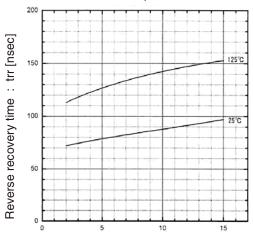
Short circuit time : 1sc [A] Short circuit ti

Gate voltage: VgE [V]

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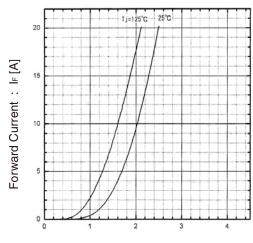
■ Characteristics

Reverse recovery time vs. Forward current VR=200V, $-di/dt=100A/\mu sec$



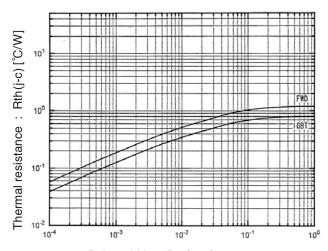
Forward current: IF [A]

Forward voltage vs. Forward current



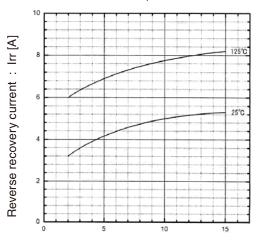
Forward Voltage: V_F[V]

Transient thermal resistance



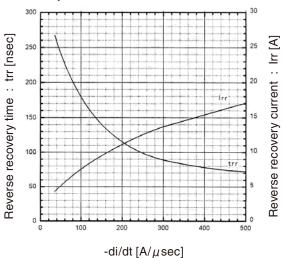
Pulse width: Pw [sec]

Reverse recovery current vs. Forward current VR=200V, $-di/dt=100A/\mu sec$



Forward current: IF [A]

Reverse recovery chracteristics vs. -di/dt $I_F=10A$, $Tj=125^{\circ}C$



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- Personal equipment
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Aeronautic equipment

Safety devices

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